

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1677	438/455,423.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/05/09 12:58
L2	414	1 and adher\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/05/09 12:59
L3	720	257/E21.122.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/05/09 12:59
L4	159	3 and adher\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/05/09 12:59
S1	4	("20020155630" "20020155630" "20030020096" "20030020096").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/12/06 11:31
S2	9966163	sos or (silicon-on-insulator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/26 06:22
S3	600095	S2 and adher\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/05/09 12:59
S4	35228	S3 and without with adhesive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/13 18:22
S5	1	S4 and no with line with defect\$ with surface	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/12/06 11:36

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S6	119	S4 and no same line same defect\$ same surface	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/12/06 11:36
S7	1	S6 and implant\$3 with hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/13 18:23
S8	2	S6 and implant\$3 same (hydrogen or H)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/12/06 13:52
S9	1159	257/200.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/12/06 13:53
S10	3850	438/14,455,423.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/05/09 12:58
S11	710	257/E21.122.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/05/09 12:59
S12	83	S11 and implant\$3 with hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/13 18:27
S13	88	S11 and (dop\$3 or implant\$3) with hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/13 18:24
S14	88	S13 and bond\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/13 18:25
S15	61	S14 and defect\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/13 18:26

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S16	3870	line adj defect\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/13 18:27
S17	14	S16 and implant\$3 with hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/13 18:27
S19	77867	(SOI or (silicon-on-insulator)or (silicon adj on) with insulator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/26 06:23
S20	17563	S19 and (bond\$3 or adher\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/26 06:25
S21	77	S20 and (line adj defect\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/26 06:26
S22	41	S21 and heat adj treatment	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/26 06:27
S24	35	S22 and (temp or temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/26 06:29
S25	1	S24 and ((defect adj free) or (no adj defect)) with surface	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/04/26 06:29